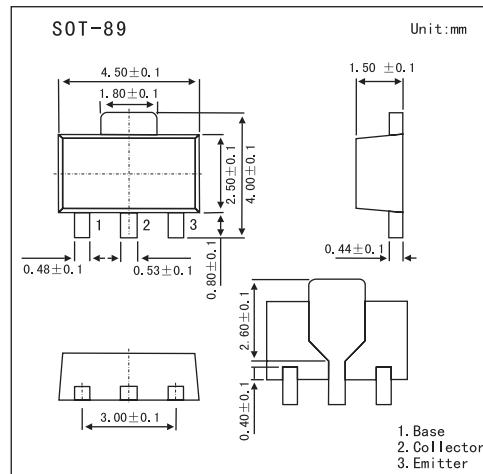


# 2SD1614

## ■ Features

- World standard miniature package.
- High dc current gain.
- Low V<sub>CE(sat)</sub>.



## ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	40	V
Collector-emitter voltage	V <sub>CEO</sub>	20	V
Emitter-base voltage	V <sub>EBO</sub>	6	V
Collector current (DC)	I <sub>c</sub>	2	A
Collector Current (pulse) *	I <sub>c</sub>	3	A
Total power dissipation	P <sub>T</sub>	2.0	W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

\* Pulse Test PW ≤ 10ms, Duty Cycle ≤ 50%.

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I <sub>CB0</sub>	V <sub>CB</sub> = 30 V, I <sub>E</sub> = 0 A			100	nA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> = 6.0 V, I <sub>C</sub> = 0 A			100	nA
DC current gain *	h <sub>FE</sub>	V <sub>CE</sub> = 2.0 V, I <sub>c</sub> = 100 mA	135	350	600	
Collector saturation voltage *	V <sub>CE(sat)</sub>	I <sub>c</sub> = 2 A, I <sub>B</sub> = 50 mA		0.3	0.5	V
Base saturation voltage *	V <sub>BE(sat)</sub>	I <sub>c</sub> = 2 A, I <sub>B</sub> = 50 mA		0.95	1.2	V
Base-emitter voltage *	V <sub>BE</sub>	V <sub>CE</sub> = 6.0 V, I <sub>c</sub> = 100 mA	650	680	750	mV
Gain bandwidth product	f <sub>T</sub>	V <sub>CE</sub> = 10 V, I <sub>E</sub> = -50 mA		200		MHz
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz		28		pF

\* Pulsed: PW ≤ 350 μs, duty cycle ≤ 2%

## ■ hFE Classification

Marking	XM	XL	XK
hFE	135~270	200~400	300~600